
2SC1515(K)

Silicon NPN Triple Diffused

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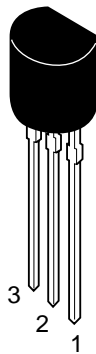
ADE-208-1055 (Z)
1st. Edition
Mar. 2001

Application

High voltage switching

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

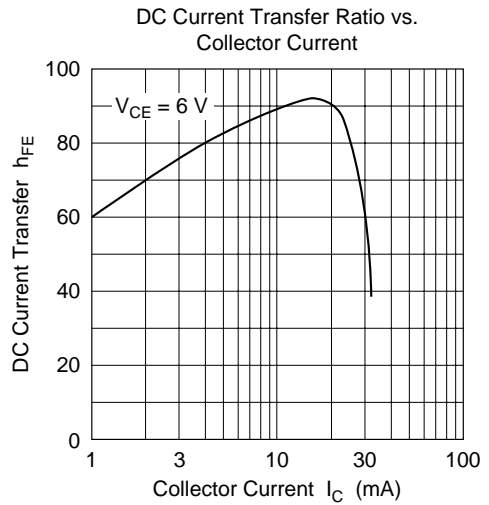
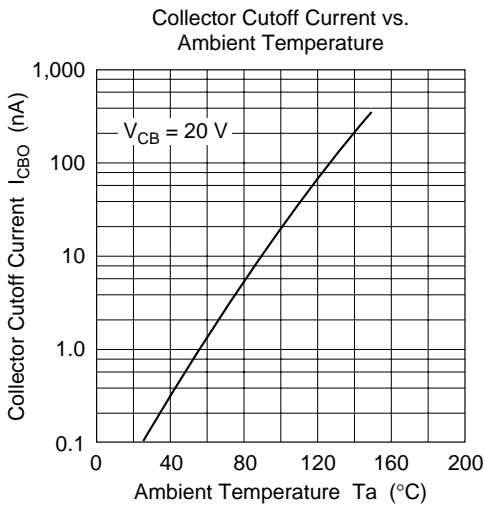
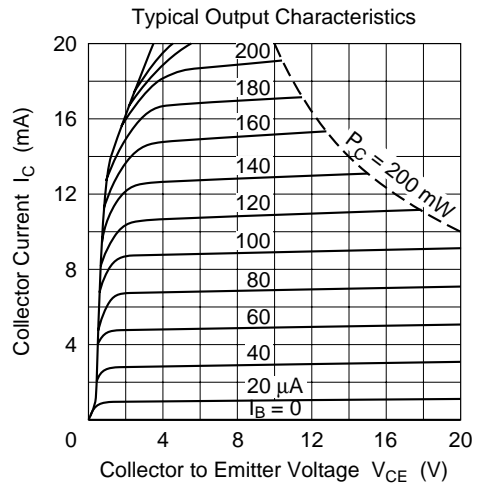
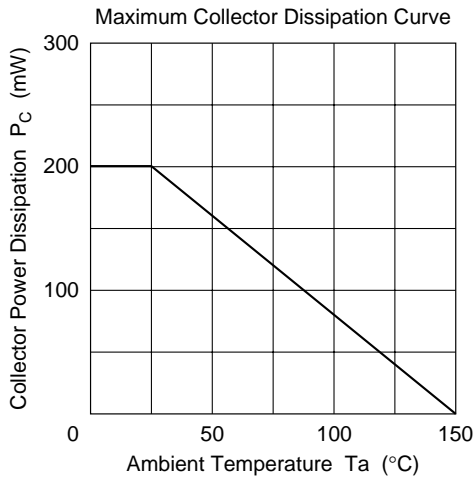
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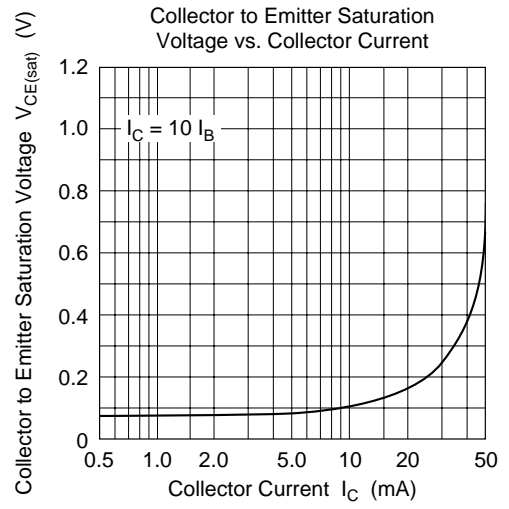
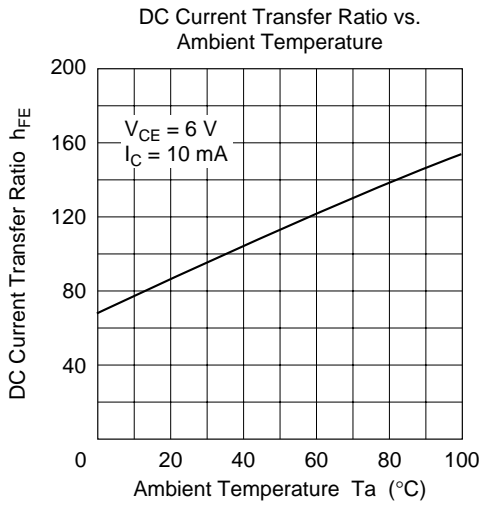
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	200	V
Collector to emitter voltage	V_{CES}	200	V
	V_{CEO}	150	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

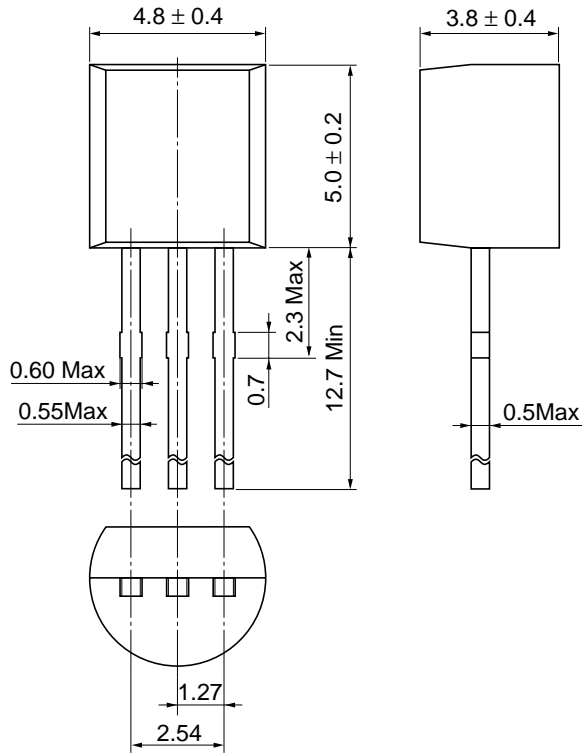
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CES}$	200	—	—	V	$I_C = 10 \mu A, R_{BE} = 0$
	$V_{(BR)CEO}$	150	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 20 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE}	30	—	300		$V_{CE} = 6 \text{ V}, I_C = 10 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Gain bandwidth product	f_T	60	—	—	MHz	$V_{CE} = 6 \text{ V}, I_C = 10 \text{ mA}$
Collector output capacitance	C_{ob}	—	—	10	pF	$V_{CB} = 6 \text{ V}, I_E = 0, f = 1 \text{ MHz}$





Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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